

1. Scope :

This specification applies to N/P silicon zener diode chips,
Device NO. SD-406D0G

2. Structure :

- 2-1. Planar type : N/P Diode
- 2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

3. Size :

- 3-1. ^{**1} Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
- 3-2. Chip thickness : 4.0 ± 1.0 mils (0.100 ± 0.0254 mm).
- 3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
- 3-4. ^{**2} Bonding pad : 4.8 mils x 4.8 mils (0.122 mm x 0.122 mm).
- 3-5. Pattern drawing : Refer to the attached drawing.

^{**1} Including scribing line. The chip size is about $(0.150 \pm 0.015)^2$ mm² after dicing.

^{**2} The wire bonding pad dimension is $(0.122 \pm 0.015)^2$ mm² after etching.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I _R	V _R =48V E _e =0mW/cm ²			100	nA
Zener Voltage	V _Z	I _Z =5mA E _e =0mW/cm ²	50			V
Forward Voltage	V _f	I _F =20mA E _e =0mW/cm ²			1.2	V

